NSN 5961-01-351-1947

Unitized Semiconductor Devices - Page 1 of 1

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Inclosure Material:

Ceramic

Overall Length:

1.000 inches

Overall Height:

Between 0.030 inches and 0.115 inches

Overall Width:

0.300 inches

Component Name And Quantity:

4 transistor

Mounting Method:

Terminal

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

75.0 collector to base voltage/static/emitter open all transistor and 50.0 collector to emitter voltage/static/base open all transistor and 6.0 emitter to base voltage, static, collector open all transistor

Current Rating Per Characteristic:

800.00 milliamperes source cutoff current all transistor

Power Rating Per Characteristic:

0.4 watts small-signal input power, common-collector preset all transistor

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius ambient air

Special Features:

All transistor junction pattern arrangement: npn

Test Data Document:

81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

14 pin

Specification Data:

81349-mil-prf-19500/559 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

A110a0

Mil-std (military Standard):

Mil-prf-19500 spec.